

## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-3.8 -2.9	Α
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-11	Α

### **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_{D}$	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{ hetaJA}$	115	°C/W
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

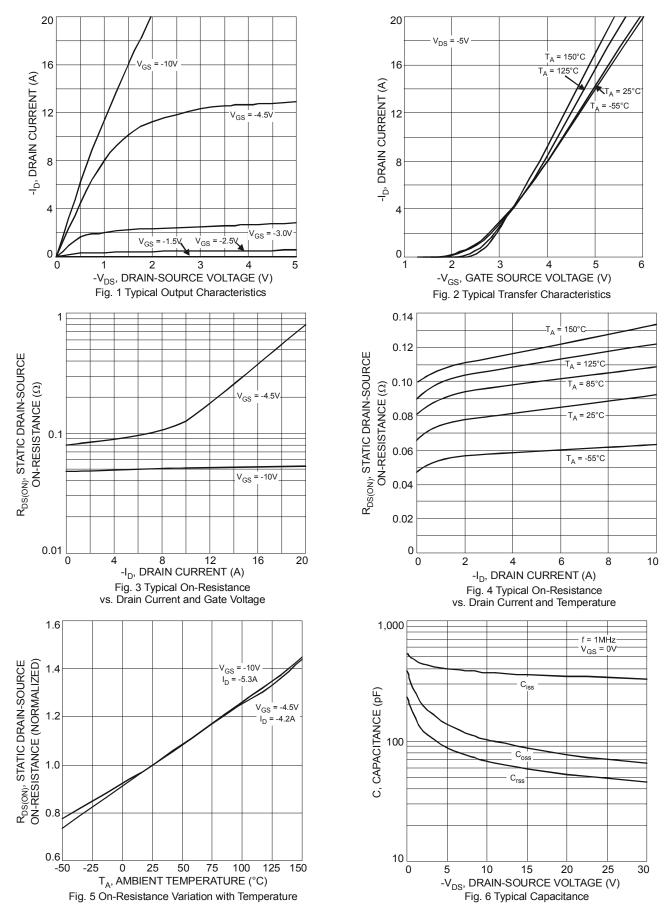
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					-	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	l	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	_	_	-800	nA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	-1.8	-2.1	V	$V_{DS} = V_{GS}$ , $I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	56 98	70 120	mΩ	$V_{GS}$ = -10V, $I_D$ = -3.8A $V_{GS}$ = -4.5V, $I_D$ = -3.0A
Forward Transfer Admittance	Y <sub>fs</sub>	_	3.6	_	S	$V_{DS} = -5V, I_D = -2.7A$
Diode Forward Voltage (Note 6)	V <sub>SD</sub>		_	-1.26	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.7A
DYNAMIC CHARACTERISTICS (Note 8)				•		
Input Capacitance	C <sub>iss</sub>	_	336	1008	pF	
Output Capacitance	Coss	_	70	210	pF	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>	_	49	147	pF	1
Gate Resistance	$R_G$	_	4.6	_	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	$Q_{g}$	_	4.0	8.0	nC	$V_{DS}$ = -15V, $V_{GS}$ = -4.5V, $I_D$ = -3.8A
		_	7.8	_		V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A
Gate-Source Charge	$Q_{gs}$	l	1.0	_		
Gate-Drain Charge	$Q_{gd}$		2.5	_		
Turn-On Delay Time	t <sub>d(on)</sub>		6.0	12.0	ns	$V_{DS}$ = -15V, $V_{GS}$ = -10V, $I_{D}$ = -1A, $R_{G}$ = 6.0 $\Omega$
Rise Time	t <sub>r</sub>		5.0	10.0		
Turn-Off Delay Time	t <sub>d(off)</sub>		17.6	35.2		
Fall Time	t <sub>f</sub>		9.5	19.0		

Notes: 5. Device mounted on FR-4 PCB on 2 oz., 0.5 in.<sup>2</sup> copper pads and  $t \le 5$  sec.

6. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .

7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.







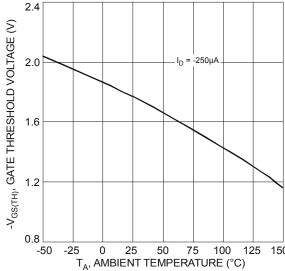
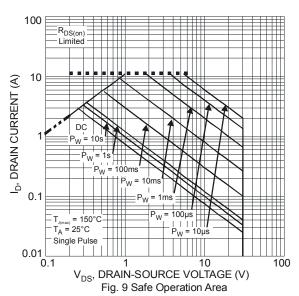
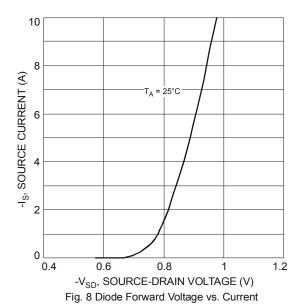


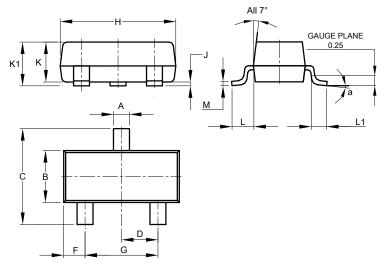
Fig. 7 Gate Threshold Variation vs. Ambient Temperature





## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

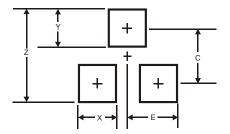


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
α	8°				
All	All Dimensions in mm				



#### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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